Bl (& l (

Vi g h

EgdY Xi H b b Vgn

6 eeaXVi dch

a XigXVa VgVXi ghi Xh

EVgVb i g	dcYi dch	Hnb Wda	KVa h			Jc i
			B c	I ne	BVm	
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					
	℃					

I gb Va VgVXi ghi Xh

EVgVb i g	dcYi dch	Hnb Wda	KVa h			Jc i
			B c	I ne	BVm	

DgY gc c dgb Vi dc

k X	BVg c	EVX V	L i	cc g dm	E g Vgdc

I ne XVa a XigXVa I gb Va VgVXi ghi Xh

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

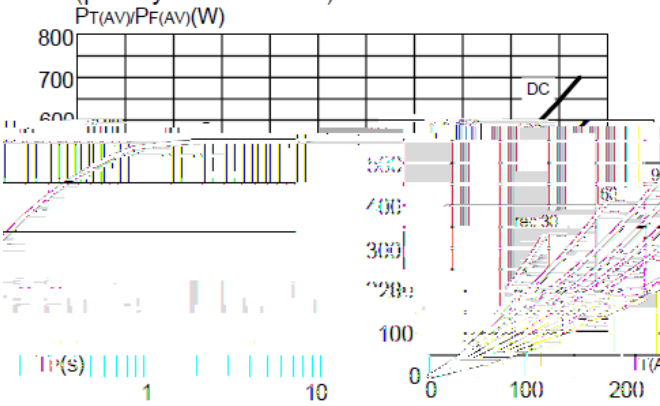


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

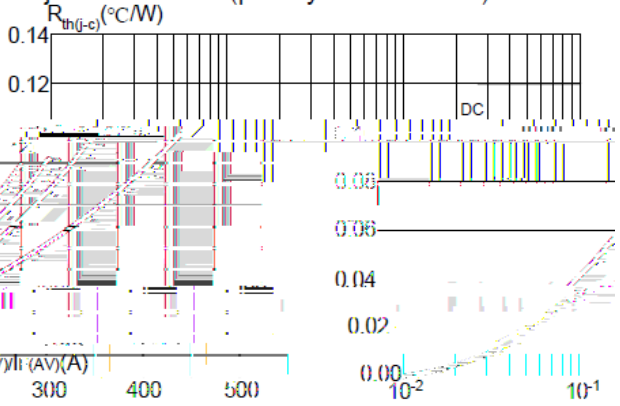


FIG.3: Forward characteristics (per thyristor or diode)

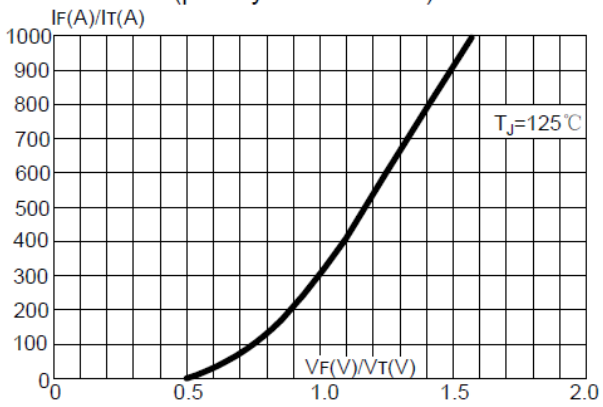


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

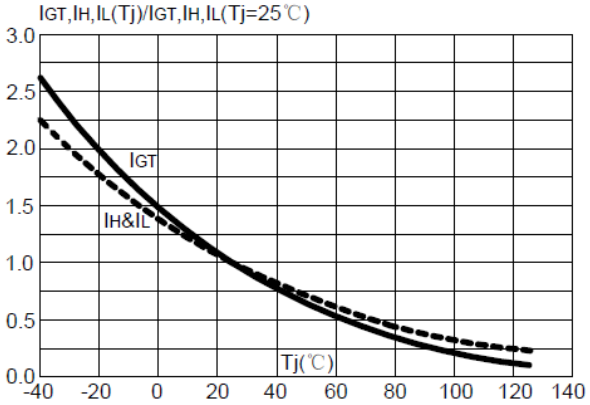
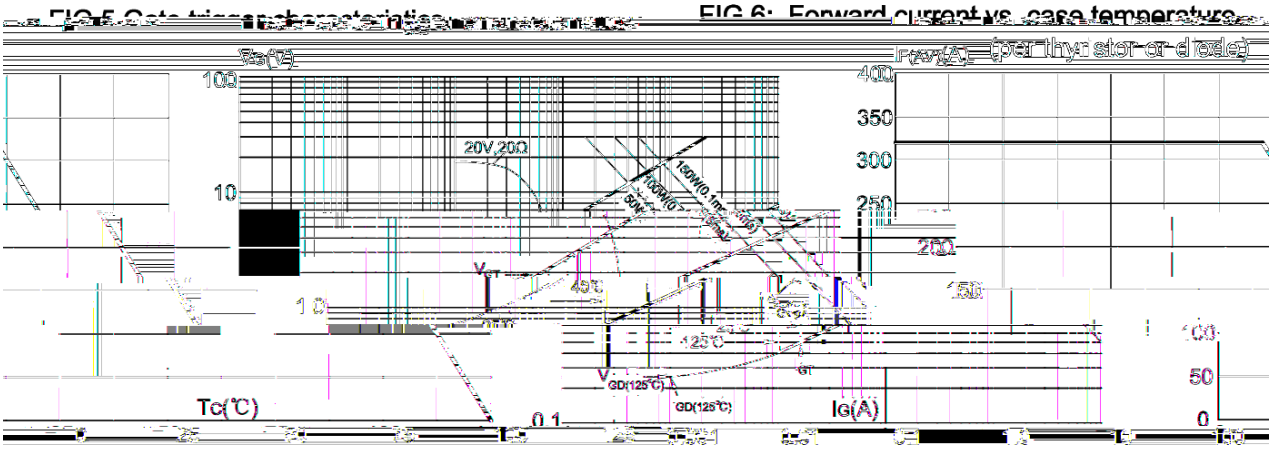
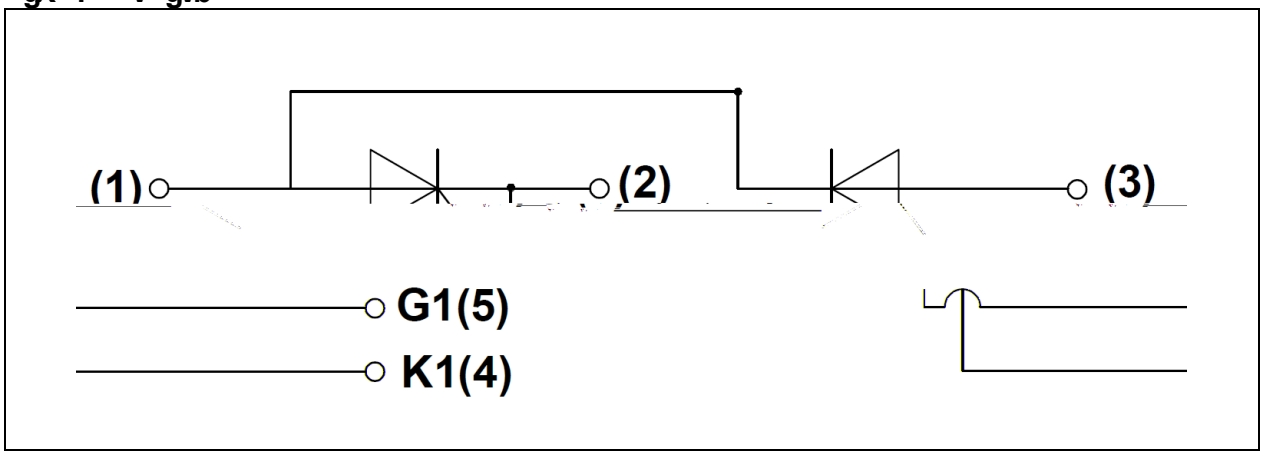


FIG.5 Gate trigger characteristics

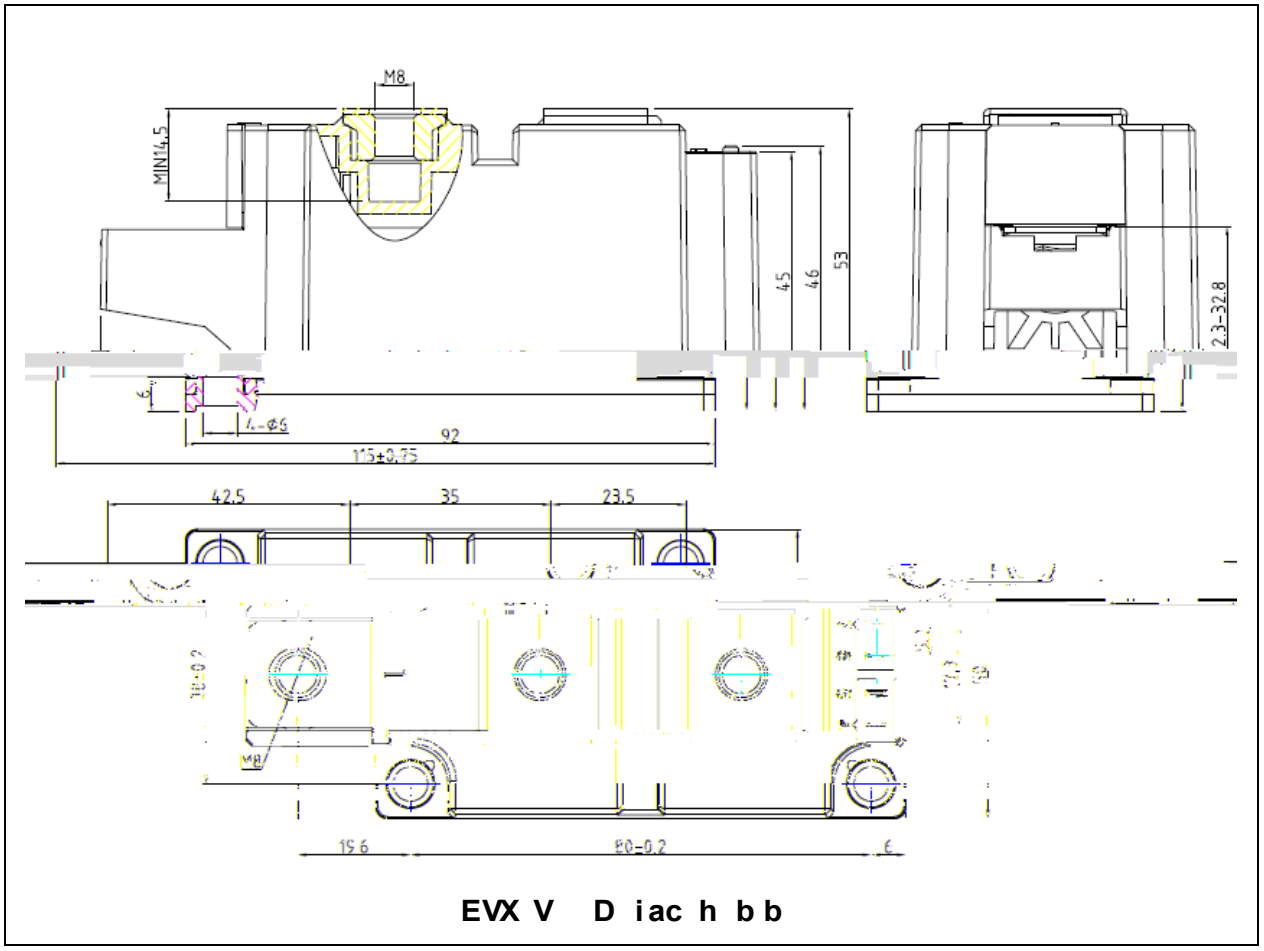
FIG.6: Forward current vs. case temperature



gX i V gVb



EVX V D iac h b b



EVX V D iac h b b